

1. Scope :

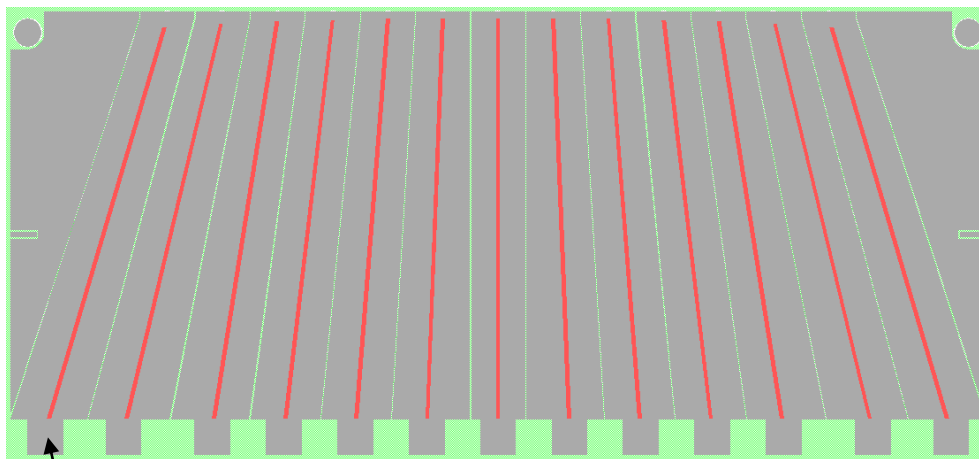
This specification applies to PIN silicon photodiode array chips,
Device No. PD-00532-B.

2. Structure :

- 2-1. Type : 13 elements PIN diode array.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy.
Back side (Cathode) : Gold.

3. Size :

- 3-1. Chip size (including scribe line) : 19.65 mm x 9.05 mm.
- 3-2. Chip thickness : 0.400 ± 0.038 mm.
- 3-3. Active width : 0.1 mm (as to below red color of drawing)
- 3-4. Bonding pad (Anode) : 0.7 mm x 0.7mm.
- 3-5. Pattern drawing : refer to below drawing.



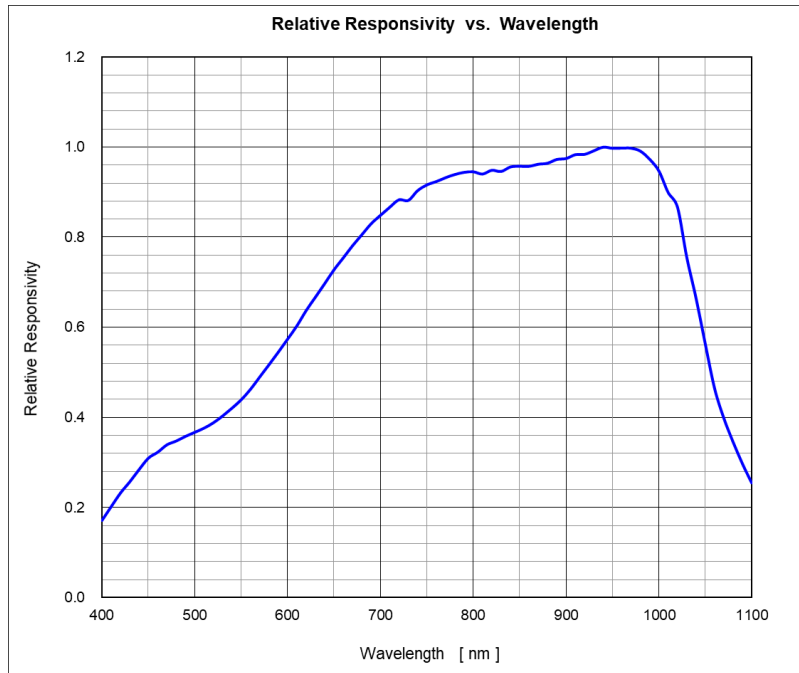
Anode bonding pad x 13

4. Electro-optical characteristics_ one element (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
* Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			30	nA
* Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu A$ $E_e=0mW/cm^2$	30			V

*Based on 100% probing

5. Relative spectral responsivity



*bare chip measured with integrating sphere, for reference only.